Datasheet



N-channel SiC power MOSFET

V _{DSS}	750V
$R_{DS(on)}$ (Typ.)	13mΩ
I _D *1	98A
P_D	267W

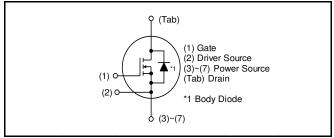
Outline



Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

•Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- · Induction heating
- Motor drives

Packaging specifications

Packing Reel size (mm)	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	1000
	Taping code	TL
	Marking	SCT4013DW7

◆Absolute maximum ratings (T_{vi} = 25°C unless otherwise specified.)

Parameter		Symbol	Value	Unit	
Drain - source voltage		V_{DSS}	750	V	
Continuous drain ,	V - V	$T_c = 25^{\circ}C$	I _D , I _S *1	98	Α
and source current	$V_{GS} = V_{GS_on}$	T _c = 100°C		69	Α
Pulsed drain current	$V_{GS} = V_{GS_on}$	$T_c = 25^{\circ}C$	I _{D,pulse} *2	233	Α
Body diode pulsed forward	ard current	$T_c = 25^{\circ}C$	I _{S,pulse} *1,*3	98	Α
Body diode surge forward current V _{GS}		$V_{GS} = 0 V$	I _{S,pulse} *1,*4	233	Α
Gate - source voltage (DC)		V_{GSS_DC}	-4 to +21	V	
Gate - source surge voltage (t _{surge} < 300ns)		V _{GSS_surge} *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		${\sf V_{GS_on}}^{*6}$	+15 to +18	V	
Recommended turn-off gate - source drive voltage		V_{GS_off}	0	V	
Virtual junction temperature		T_{vj}	175	°C	
Range of storage tempe	erature		T_{stg}	-40 to +175	°C

ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	c		Values		
r didilletei	Syllibol	Conditions	Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V	$V_{GS} = 0 \text{ V}, I_D = 18.6 \text{mA}$				V	
	(BR)DSS	$T_{vj} = 25^{\circ}C$	750	-	-	V	
		$V_{GS} = 0 \text{ V}, V_{DS} = 750 \text{V}$					
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	80	μA	
Diam current		T _{vj} = 150°C	-	10	-		
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +21V$, $V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	$V_{GS(th)}^{*7}$	$V_{DS} = 10V, I_D = 30.8 mA$	2.8	-	4.8	V	
		$V_{GS} = 18V, I_{D} = 58A$				_	
Static Drain - Source on - state resistance	R _{DS(on)} *8	$T_{vj} = 25^{\circ}C$	-	13.0	16.9	mΩ	
on state resistance		T _{vj} = 150°C	-	22.2	-		
Gate input resistance	R_{G}	f = 1MHz, open drain	-	1	-	Ω	

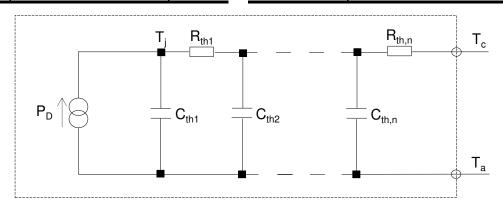
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}^{}^{*9}}$	-	0.43	0.56	K/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	4.1 ×10 ⁻²	
R _{th2}	1.8 ×10 ⁻¹	K/W
R _{th3}	2.1 ×10 ⁻¹	

Symbol	Value	Unit
C _{th1}	1.2 ×10 ⁻³	
C _{th2}	5.0 ×10 ⁻³	Ws/K
C _{th3}	4.7 ×10 ⁻²	



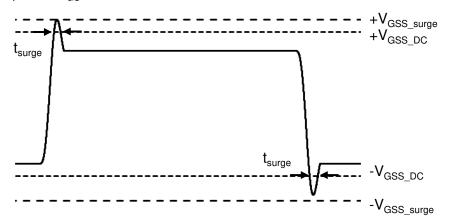
ullet Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Doromotor	Cumbal	ol Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	g _{fs} *8	$V_{DS} = 10V, I_{D} = 58A$	-	32	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	4580	ı	
Output capacitance	C _{oss}	V _{DS} = 500V	-	203	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	10	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	ı	263	ı	pF
Total Gate charge	Q_g^{*8}	$V_{DS} = 500V$ $I_{D} = 58A$	-	170	-	
Gate - Source charge	Q _{gs} *8	$V_{GS} = 18V$	ı	39	ı	nC
Gate - Drain charge	Q _{gd} *8	See Fig. 1-1, 1-2.	-	42	-	
Turn - on delay time	t _{d(on)} *8	$V_{DS} = 500V$	ı	17	ı	
Rise time	t _r *8	$I_D = 58A$ $V_{GS} = +18V / 0V$	ı	32	ı	ns
Turn - off delay time	t _{d(off)} *8	$R_G = 6.8\Omega$, L = 250µH E_{on} includes diode	-	82	-	115
Fall time	t _f *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	17	-	
Turn - on switching loss	E _{on} *8	See Fig. 2-1, 2-2, 2-3.	-	500	-	11.1
Turn - off switching loss	E _{off} *8		-	310	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vi} = 25°C unless otherwise specified)

Daramatar	Symbol Conditions -	Values			l lmit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V _{SD} *8	$V_{GS} = 0V, I_{S} = 58A$	ı	3.3	ı	V
Reverse recovery time	t _{rr} *8	$I_F = 58A$ $V_B = 500V$	ı	16	ı	ns
Reverse recovery charge	Q _{rr} *8	$di/dt = 3300A/\mu s$	ı	290	ı	nC
Peak reverse recovery current	I _{rrm} *8	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	36	-	А

- *1 Limited by maximum T_{vj} and for Max. R_{thJC}.
- *2 Pulse width and duty cycle are limited by $T_{v_j,max}$.
- *3 Only for body-diode, Repititive pulse, PW ≤ 1.5µs, Duty cycle ≤ 5%
- *4 When used as a protective function, PW \leq 10 μ s
- *5 Example of acceptable V_{GS} waveform



Please note especially when using driver source that $V_{\text{GSS_surge}}$ must be in the range of absolute maximum rating.

- *6 Please be advised not to use SiC-MOSFETs with V_{GS} below 10V as doing so may cause thermal runaway.
- *7 Tested after applying $V_{GS} = 21V$ for 100ms.
- *8 Pulsed
- *9 Measured conformable to JESD51-14.

See the application note "rthjc_measurement_and_usage_an-e.pdf". Link

URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc_measurement_and_usage_an-e.pdf

Fig.1 Power Dissipation Derating Curve

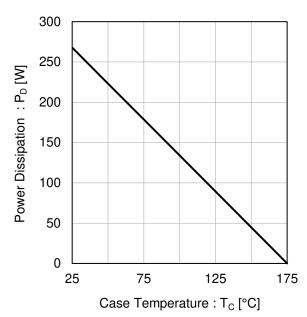


Fig.2 Maximum Safe Operating Area

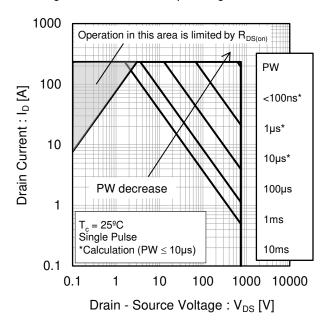
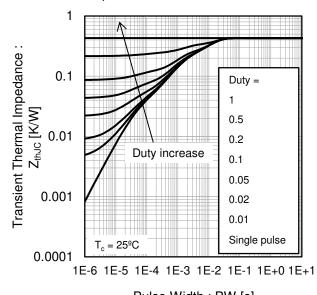
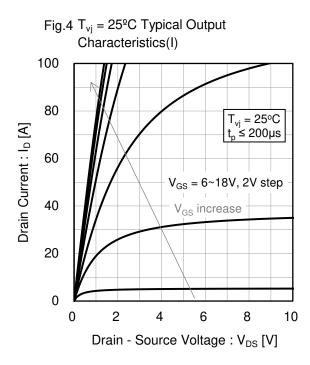


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width



Pulse Width: PW [s]



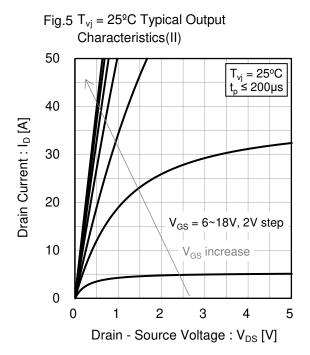
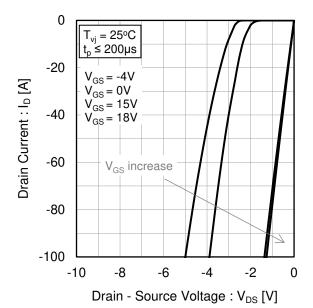
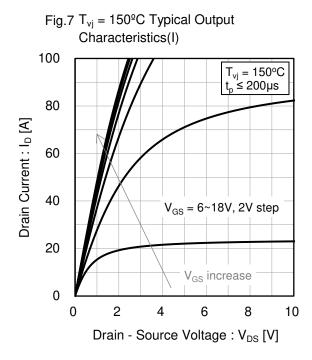
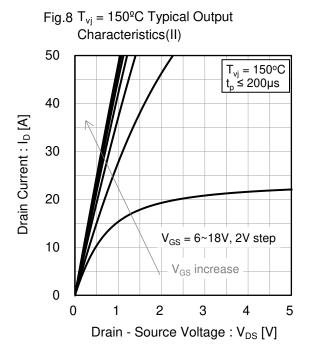
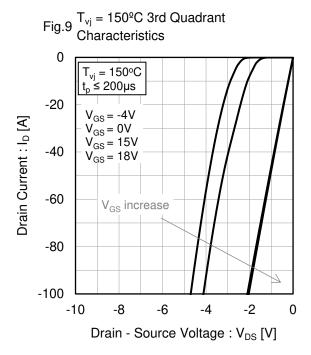


Fig.6 T_{vj} = 25°C 3rd Quadrant Characteristics









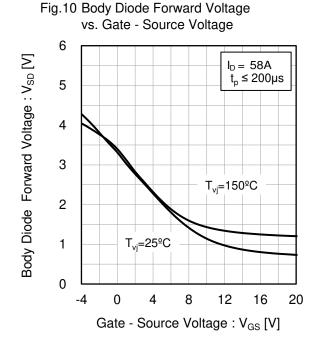


Fig.11 Typical Transfer Characteristics (I)

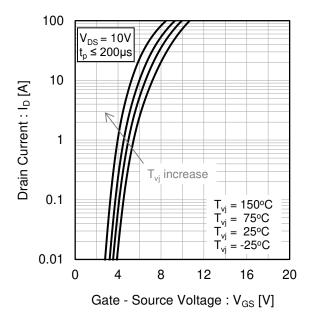


Fig.12 Typical Transfer Characteristics (II)

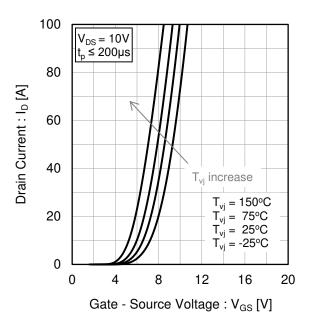


Fig.13 Gate Threshold Voltage vs. Virtual Junction Temperature

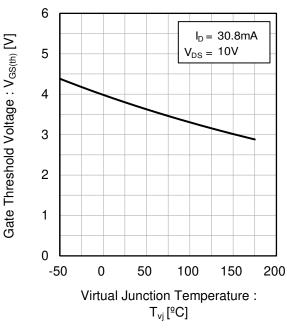
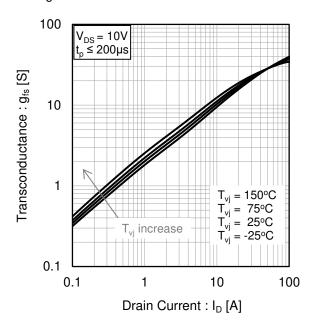
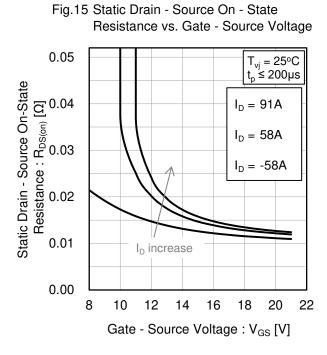


Fig.14 Transconductance vs. Drain Current





Resistance vs. Virtual Junction Temperature 0.05 V_{GS} = 18V t_p ≤ 200µs = 91A= 58A $I_D = -58A$ $I_{\rm D}$ increase 0.00 -50 0 100 50 150 200 Virtual Junction Temperature: T_{vi} [ºC]

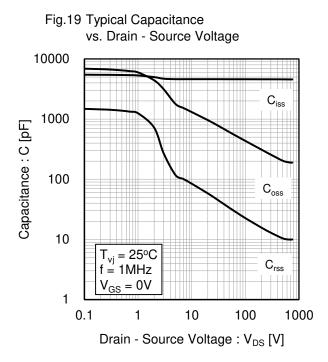
Fig.16 Static Drain - Source On - State

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current = 150°C $T_{vj} = 125^{\circ}C$ Static Drain - Source On-State $T_{vj} = 75^{\circ}C$ $T_{vj} = 25^{\circ}C$ $T_{vj} = -25^{\circ}C$ Resistance : $R_{DS(on)}\left[\Omega\right]$ 0.1 0.01 T_{vi} increase V_{GS} = 18V t_p ≤ 200µs 0.001 10 100 Drain Current: ID [A]

Voltage vs. Virtual Junction Temperature 1.1 Normalized Drain - Source **Breakdown Voltage** 1.0 $V_{GS} = 0 V$ $I_{\rm D} = 18.6 \, \rm mA$ 0.9 -50 0 50 100 150 200 Virtual Junction Temperature: T_{vi} [ºC]

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Fig.18 Normalized Drain - Source Breakdown



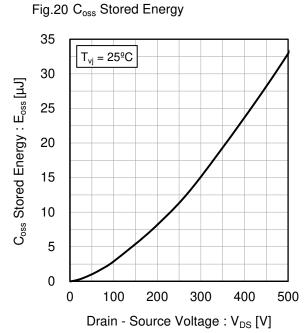
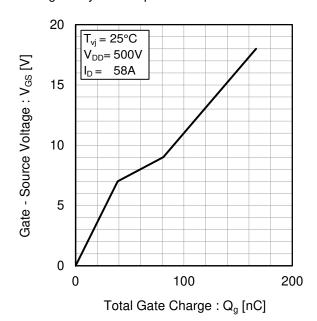
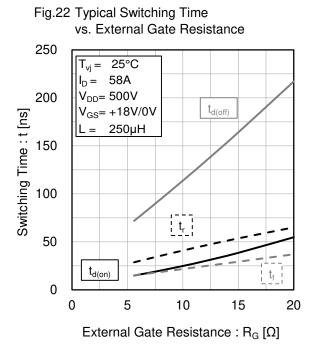


Fig.21 Dynamic Input Characteristics





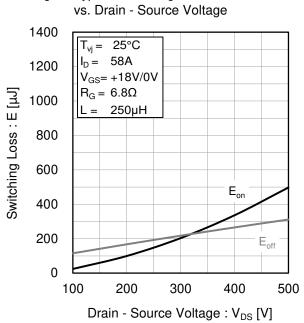
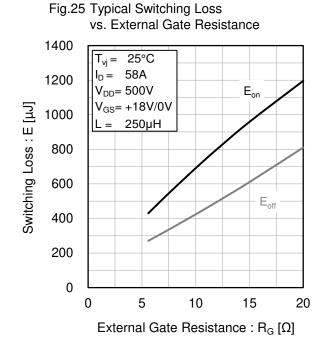


Fig.23 Typical Switching Loss

Fig.24 Typical Switching Loss vs. Drain Current 1400 $T_{vj} =$ 25°C $V_{DD} = 500V$ 1200 $V_{GS} = +18V/0V$ $R_G = 6.8\Omega$ Switching Loss: E [µJ] 1000 250µH L = 800 E_{on} 600 400 $\mathsf{E}_{\mathsf{off}}$ 200 0 0 20 40 60 80 100 Drain Current: I_D [A]



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• Measurement circuits and waveforms

Fig.1-1 Gate Charge Measurement Circuit

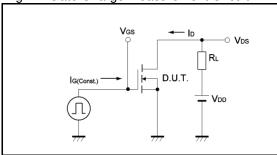


Fig.2-1 Switching Characteristics Measurement Circuit

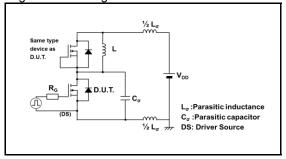


Fig.2-3 Waveforms for Switching Energy Loss

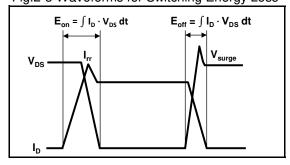


Fig.3-1 Reverse Recovery Time Measurement Circuit

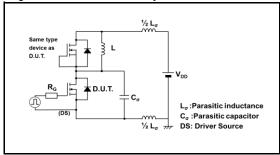


Fig.1-2 Gate Charge Waveform

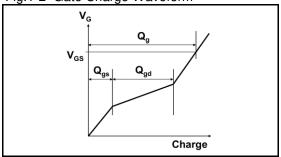


Fig.2-2 Waveforms for Switching Time

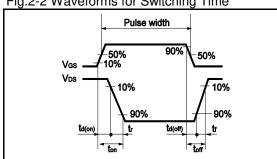
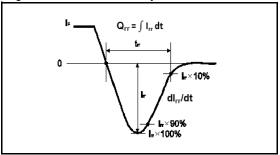
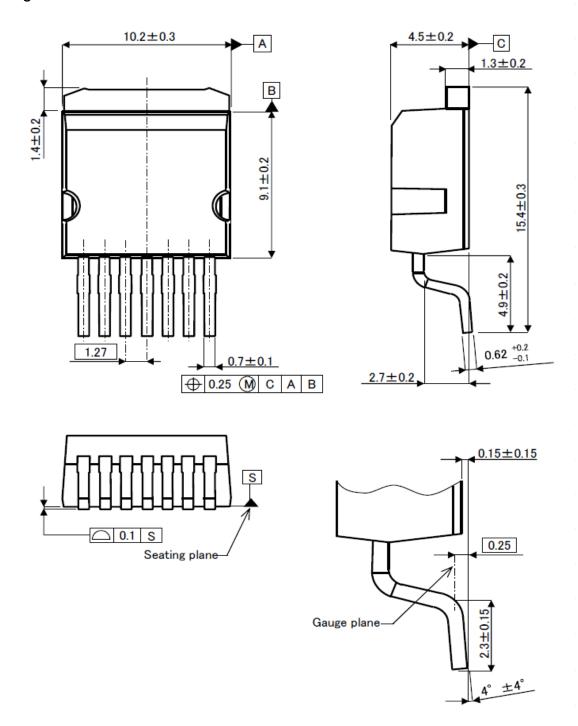


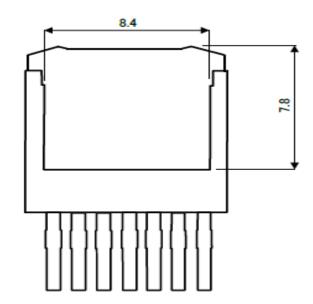
Fig.3-2 Reverse Recovery Waveform



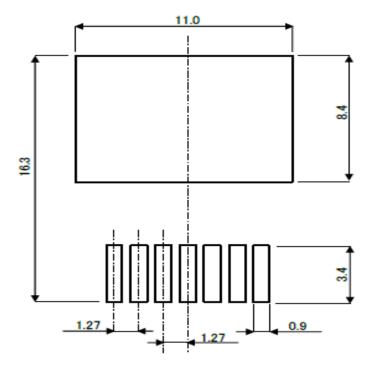
●Package Dimensions



Unit: mm

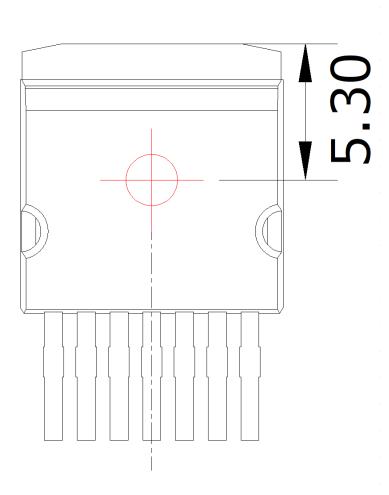


RECOMMENDED FOOTPRINT DIMENSIONS



Unit: mm

●Die Bonding Layout



: Die position

- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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